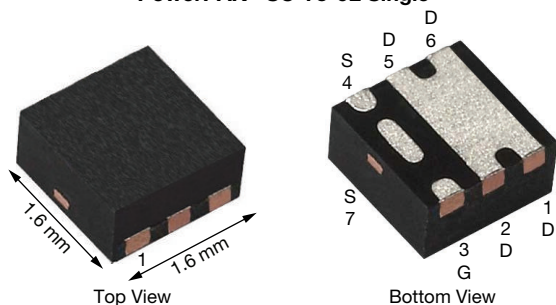


P-Channel 30 V (D-S) MOSFET

PowerPAK® SC-75-6L Single

Marking code: BP

PRODUCT SUMMARY

V_{DS} (V)	-30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -10$ V	0.065
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5$ V	0.080
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5$ V	0.125
Q_g typ. (nC)	6.6
I_D (A) ^a	-4.5
Configuration	Single

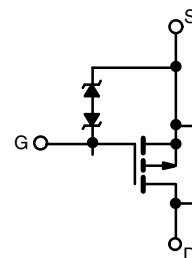
FEATURES

- Thermally enhanced PowerPAK® SC-75 package
 - Small footprint area
 - Low on-resistance
 - Thin 0.75 mm profile
- Typical ESD protection (MOSFET): 1500 V (HBM)
- 100 % R_g tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Portable devices such as smart phones, tablet PCs, and mobile computing
 - Battery charger switch
 - Buck converter
 - Power management
 - Load switch



P-Channel MOSFET

ORDERING INFORMATION

Package	PowerPAK SC-75
Lead (Pb)-free and halogen-free	SiB4317EDK-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	-30	V
Gate-source voltage	V_{GS}	± 12	V
Continuous drain current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	-4.5 ^a
		$T_C = 70$ °C	-4.5 ^a
		$T_A = 25$ °C	-4.3 ^{b, c}
		$T_A = 70$ °C	-3.5 ^{b, c}
Pulsed drain current ($t = 300$ μ s)	I_{DM}	-15	A
Continuous source-drain diode current (MOSFET diode conduction)	I_S	$T_C = 25$ °C	-4.5 ^a
		$T_A = 25$ °C	-1.63 ^{b, c}
Maximum power dissipation	P_D	$T_C = 25$ °C	10
		$T_C = 70$ °C	6.4
		$T_A = 25$ °C	1.95 ^{b, c}
		$T_A = 70$ °C	1.25 ^{b, c}
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^{d, e}		260	°C

Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

**THERMAL RESISTANCE RATINGS**

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^{a, b}	$t \leq 5$ s	R_{thJA}	51	64	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	10	12.5	

Notes

a. Surface mounted on 1" x 1" FR4 board

b. Maximum under steady state conditions is 100 °C/W

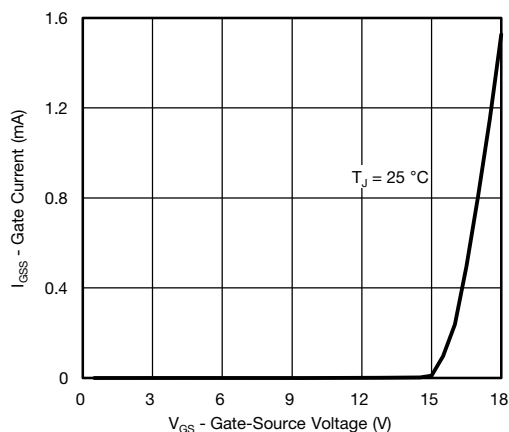
SPECIFICATIONS ($T_J = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-30	-	-	V	
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = -250 μA	-	-23	-	mV/°C	
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J		-	2.7	-		
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.6	-	-1.3	V	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 4.5 V	-	-	± 0.5	μA	
		V _{DS} = 0 V, V _{GS} = ± 12 V	-	-	± 10		
Zero gate voltage drain current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V	-	-	-1		Ω
		V _{DS} = -30 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V, I _D = -3 A	-	0.054	0.065	Ω	
		V _{GS} = -4.5 V, I _D = -2 A	-	0.065	0.080		
		V _{GS} = -2.5 V, I _D = -1 A	-	0.095	0.125		
Forward transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -3 A	-	9	-	S	
Dynamic ^b							
Input capacitance	C _{iss}	V _{DS} = -15 V, V _{GS} = 0 V, f = 1 MHz	-	600	-	pF	
Output capacitance	C _{oss}		-	55	-		
Reverse transfer capacitance	C _{rss}		-	50	-		
Total gate charge	Q _g	V _{DS} = -15 V, V _{GS} = -10 V, I _D = -4.2 A	-	14	23	nC	
			-	6.6	10		
		V _{DS} = -5 V, V _{GS} = -4.5 V, I _D = -4.2 A	-	1.3	-		
			-	2	-		
Gate-source charge	Q _{gs}	f = 1 MHz	1.1	5.5	11	Ω	
Gate-drain charge	Q _{gd}		-	20	40	ns	
Gate resistance	R _g	V _{DD} = -15 V, R _L = 4.4 Ω I _D ≅ -3.4 A, V _{GEN} = -4.5 V, R _g = 1 Ω	-	20	40		
Turn-on delay time	t _{d(on)}		-	23	45		
Rise time	t _r		-	10	20		
Turn-off delay time	t _{d(off)}		-	10	20		
Fall time	t _f	V _{DD} = -15 V, R _L = 4.4 Ω I _D ≅ -3.4 A, V _{GEN} = -10 V, R _g = 1 Ω	-	10	20		
Turn-on delay time	t _{d(on)}		-	25	50		
Rise time	t _r		-	7	15		
Turn-off delay time	t _{d(off)}		-				
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	-4.5	A	
Pulse diode forward current	I _{SM}		-	-	-15		
Body diode voltage	V _{SD}	I _S = -3.4 A, V _{GS} = 0 V	-	-0.9	-1.2	V	
Body diode reverse recovery time	t _{rr}	I _F = -3.4 A, di/dt = 100 A/μs, T _J = 25 °C	-	16	30	ns	
Body diode reverse recovery charge	Q _{rr}		-	8	15	nC	
Reverse recovery fall time	t _a		-	9	-	ns	
Reverse recovery rise time	t _b		-	7	-		

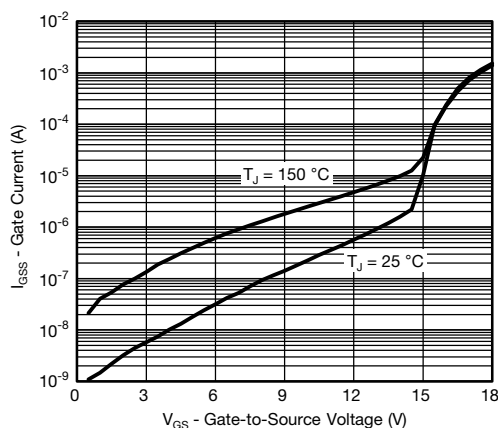
Notesa. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %

b. Guaranteed by design, not subject to production testing

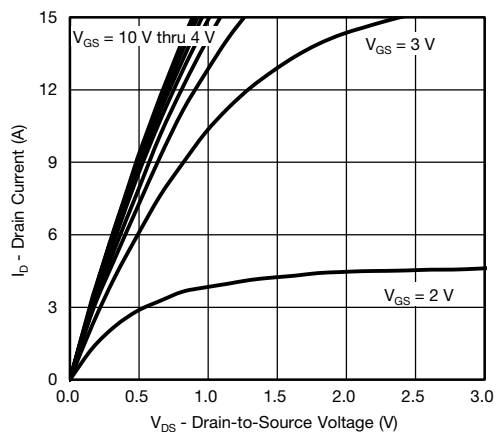
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


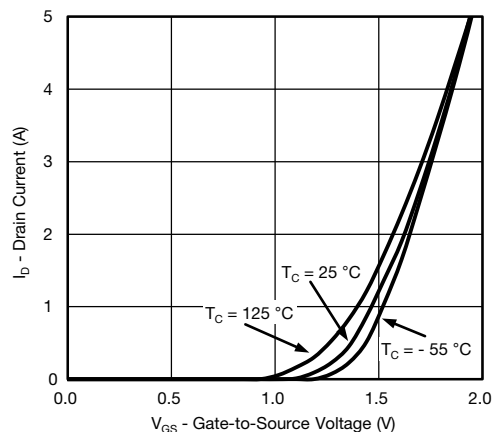
Gate-Source Voltage vs. Gate Current



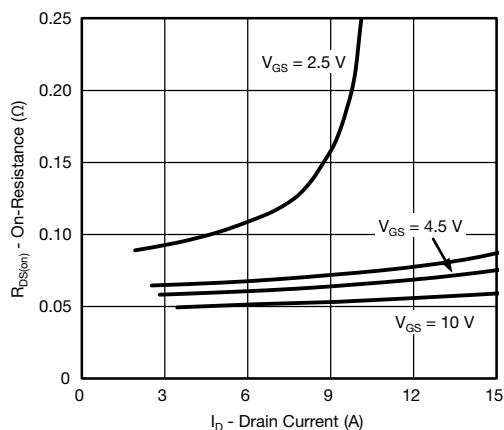
Gate-Source Voltage vs. Gate Current



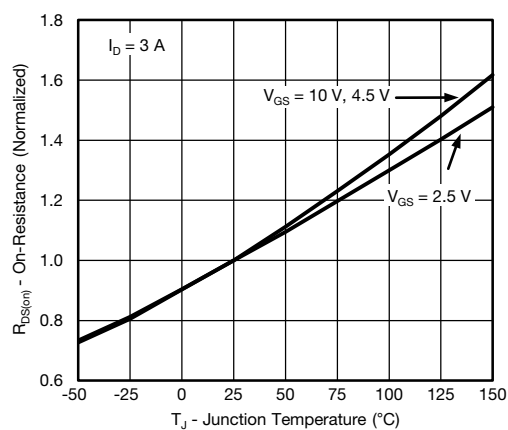
Output Characteristics



Transfer Characteristics



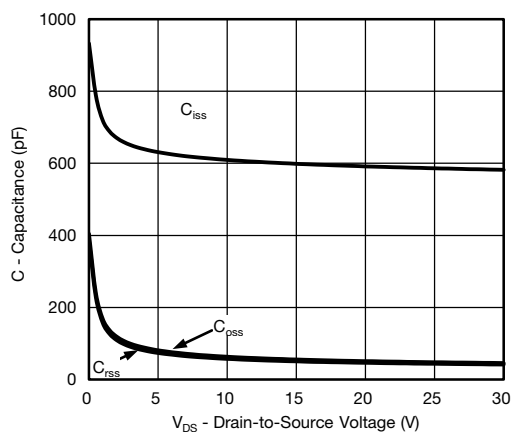
On-Resistance vs. Drain Current and Gate Voltage



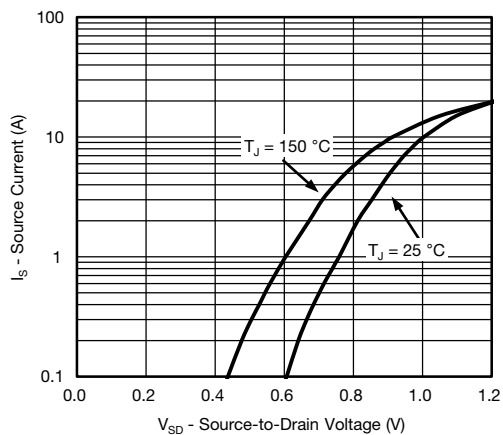
On-Resistance vs. Junction Temperature



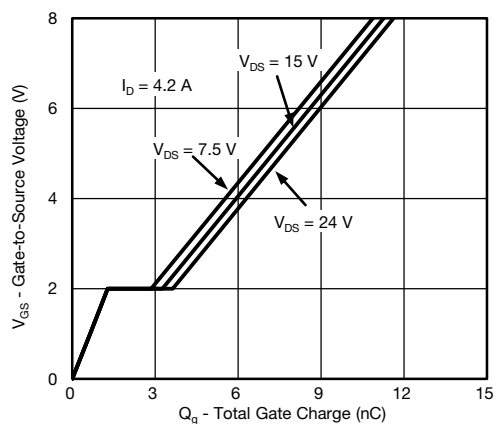
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



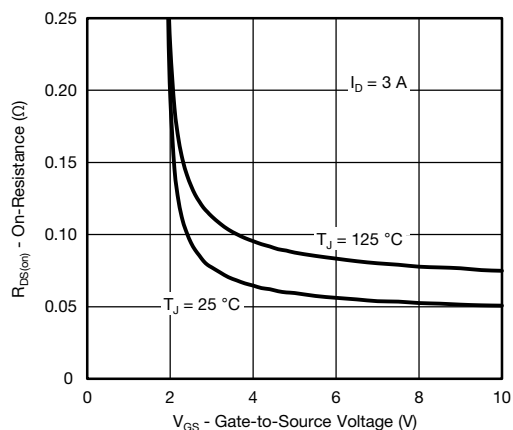
Capacitance



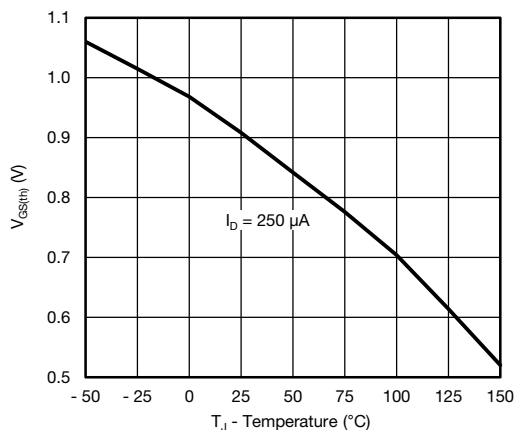
Source-Drain Diode Forward Voltage



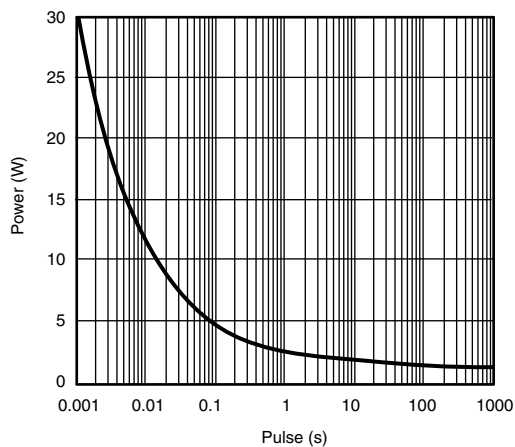
Gate Charge



On-Resistance vs. Gate-to-Source Voltage



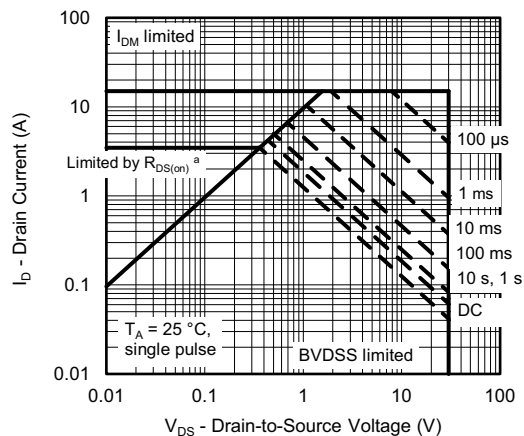
Threshold Voltage



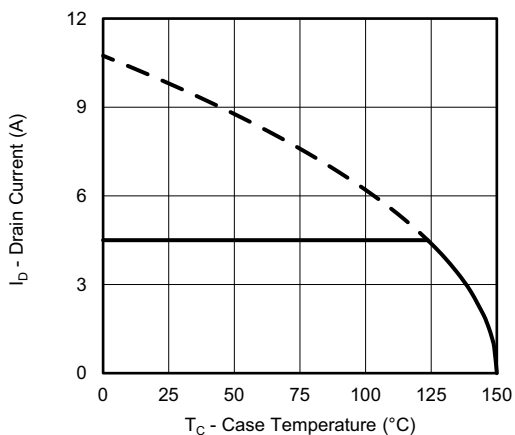
Single Pulse Power, Junction-to-Ambient



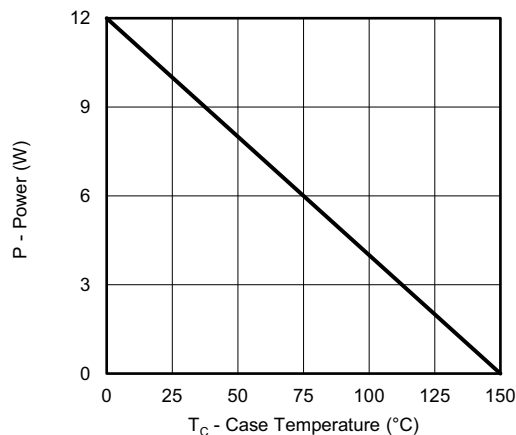
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Safe Operating Area, Junction-to-Case



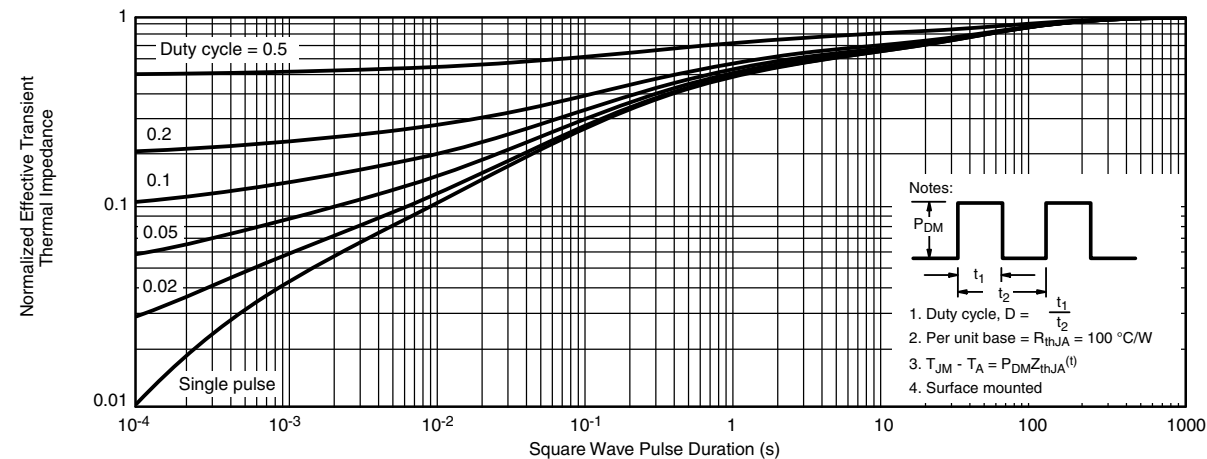
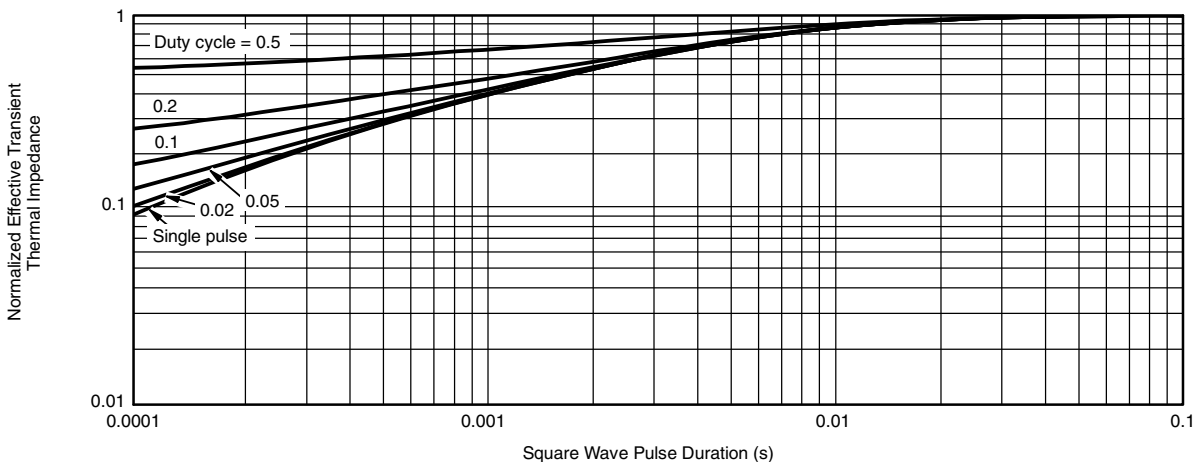
Current Derating^a



Power Derating

Note

- a. The power dissipation P_D is based on $T_J \text{ max.} = 150\text{ }^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

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